



A Product Line of Diodes Incorporated



ZXTD6717E6

COMPLEMENTARY 15V NPN & 12V PNP LOW SATURATION TRANSISTORS IN SOT26

Features and Benefits

- Pd = 1.1W in SOT26 Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

NPN Transistor

- BV_{CEO} > 15V
- I_C = 1.5A Continuous Collector Current
- Low Saturation Voltage (100mV max @ 1A)
- R_{SAT} = 135mΩ @1.5A for a Low Equivalent On-Resistance

PNP Transistor

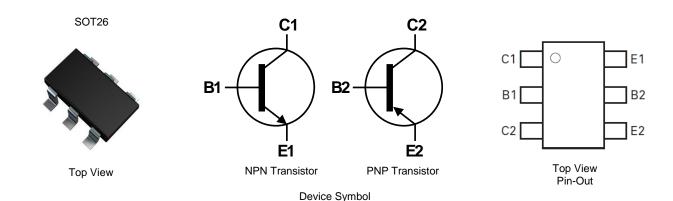
- BV_{CEO} > -12V
- I_C = -1.25A Continuous Collector Current
- Low Saturation Voltage (-140mV max @ -1A)
- $R_{SAT} = 150m\Omega @ 1.2A$ for a Low Equivalent On-Resistance

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.015 grams (Approximate)

Applications

- Efficient Driving Functions including Motors, Lamps, Relays and Solenoids
- High Output Current Switches



Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTD6717E6TA	AEC-Q101	6717	7	8	3,000
ZXTD6717E6QTA	Automotive	6717	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

 Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
 For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

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Date Code	Key												
Year	201	5	2016	2017	2018	2019	2020	202	1 20	22	2023	2024	2025
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ZXTD671	17E6		1 of 8 March 201								March 2015		

Document Number: DS33653 Rev: 4 - 2

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NPN - Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	15	V
Collector-Emitter Voltage	V _{CEO}	15	V
Emitter-Base Voltage	V _{EBO}	7	V
Peak Pulse Current	I _{CM}	5	А
Continuous Collector Current	lc	1.5	A
Base Current	IB	200	mA

PNP - Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-12	V
Collector-Emitter Voltage	V _{CEO}	-12	V
Emitter-Base Voltage	V _{EBO}	-7	V
Peak Pulse Current	I _{CM}	-3	A
Continuous Collector Current	Ic	-1.25	A
Base Current	IB	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)	_	1.1 8.8	W	
Linear Derating Factor	(Note 7)	P _D	1.7 13.6	mW/°C	
Thermal Resistance, Junction to Ambient	mal Resistance, Junction to Ambient (Note 6) (Note 7)		125 45	°C/W	
Thermal Resistance, Junction to Lead (Note 8)		R _{θJL}	95		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured

under still air conditions whilst operating in a steady-state. Two active dice running at equal power with heatsink split 50% to each collector. 7. Same as Note 6, except the device is measured at t < 5 seconds.

Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.





Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition	
OFF CHARACTERISTICS			1				
Collector-Base Breakdown Voltage	BV _{CBO}	15	—		V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	15	—	_	V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	7	—	_	V	$I_{E} = 100 \mu A, I_{C} = 0$	
Collector Cut-Off Current	I _{CBO}	_	<-1	10	nA	$V_{CB} = 10V$	
Emitter Cut-Off Current	I _{EBO}		<-1	10	nA	V _{EB} =5.6	
Emitter Cut-Off Current	ICES		<-1	10	nA	$V_{CE} = 10V$	
ON CHARACTERISTICS (Note 10)							
DC Current Gain	hfe	200 300 250 200 75 30	420 450 390 300 150 75		_	$\begin{split} I_{C} &= 10mA, \ V_{CE} = 2V \\ I_{C} &= 100mA, \ V_{CE} = 2V \\ I_{C} &= 500mA, \ V_{CE} = 2V \\ I_{C} &= 1A, \ V_{CE} = 2V \\ I_{C} &= 3A, \ V_{CE} = 2V \\ I_{C} &= 5A, \ V_{CE} = 2V \end{split}$	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	16.5 40 75 150 205	20 55 100 200 245	mV mV mV mV mV	$\begin{split} I_{C} &= 100\text{mA}, \ I_{B} = 10\text{mA} \\ I_{C} &= 250\text{mA}, \ I_{B} = 10\text{mA} \\ I_{C} &= 500\text{mA}, \ I_{B} = 10\text{mA} \\ I_{C} &= 1A, \ I_{B} = 10\text{mA} \\ I_{C} &= 1.5\text{A}, \ I_{B} = 20\text{mA} \end{split}$	
Base-Emitter Saturation Voltage	V _{BE(sat)}		0.93	1.10	V	$I_{C} = 1.5A, I_{B} = 20mA$	
Base-Emitter Turn-On Voltage	V _{BE(on)}		0.865	1.10	V	I _C = 1.5A, V _{CE} = 2V	
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C _{obo}		15	_	pF	V _{CB} = 10V, f = 1.0MHz	
Current Gain Bandwidth Product	f _T		180		MHz	$I_{C} = 50 \text{mA}, V_{CE} = 10 \text{V}$ f = 100MHz	
SWITCHING CHARACTERISTICS							
Turn-On Time	t _{on}		50		ns	$I_{C} = 1A, V_{CC} = 10V$	
Turn-Off Time	t _{off}	_	250	_	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$	

NPN - Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

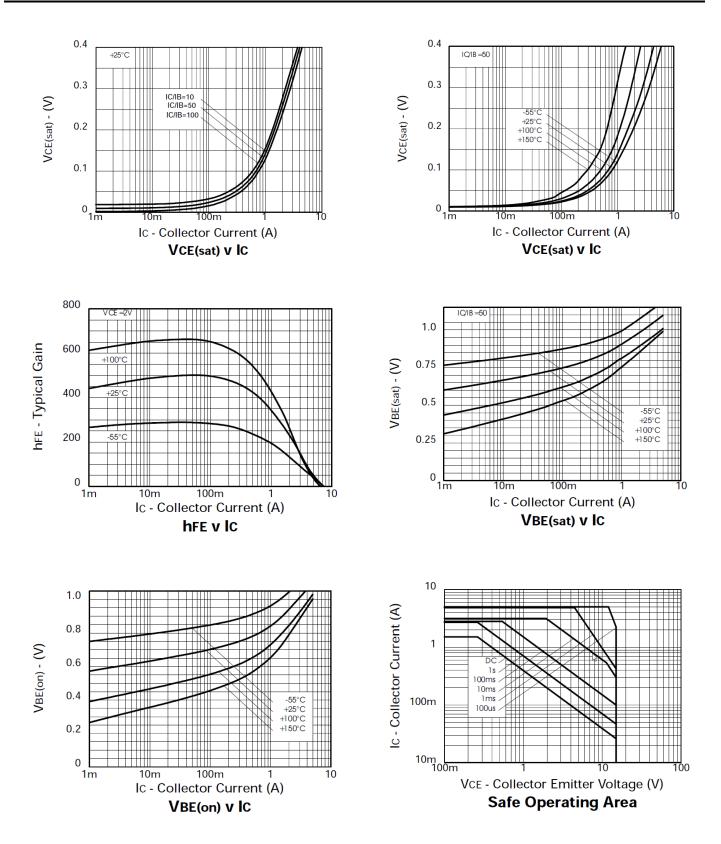
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 $\mu s.$ Duty cycle \leq 2%.



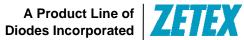


LETEX

NPN - Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







PNP - Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

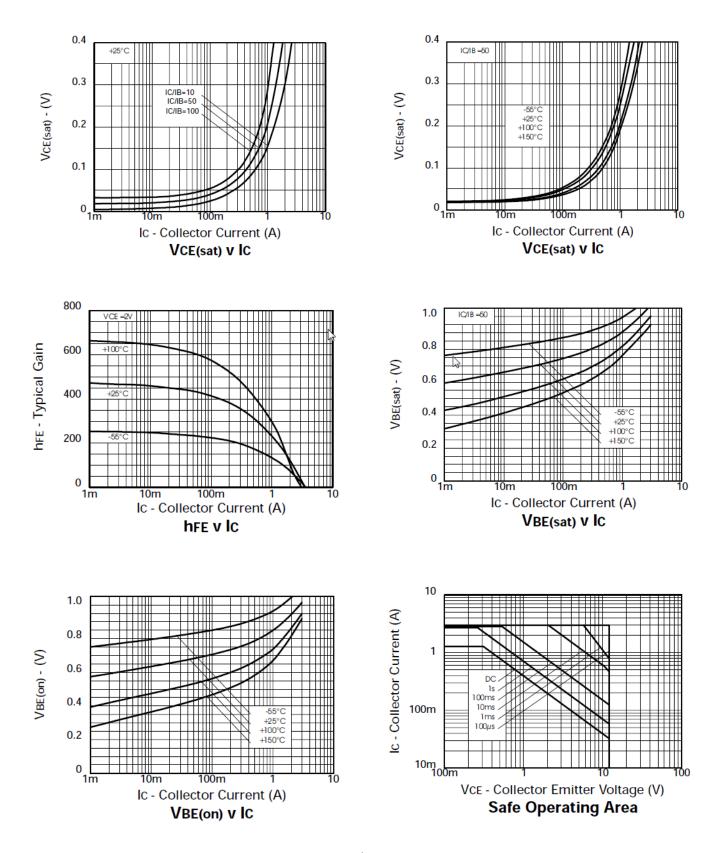
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS	1 2					1
Collector-Base Breakdown Voltage	BV _{CBO}	-12			V	$I_{\rm C} = -100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-12	_		V	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7		_	V	$I_{E} = -100 \mu A, I_{C} = 0$
Collector Cut-Off Current	I _{CBO}	_	<-1	-10	nA	$V_{CB} = -10V$
Emitter Cut-Off Current	I _{EBO}	_	<-1	-10	nA	V _{EB} = -5.6V
Emitter Cut-Off Current	I _{CES}	_	<-1	-10	nA	V _{CE} = -10V
ON CHARACTERISTICS (Note 11)						
DC Current Gain	hfe	300 300 200 125 75 30	490 450 340 250 140 80			$\begin{split} I_{C} &= -10 mA, V_{CE} = -2V \\ I_{C} &= -100 mA, V_{CE} = -2V \\ I_{C} &= -500 mA, V_{CE} = -2V \\ I_{C} &= -1.25A, V_{CE} = -2V \\ I_{C} &= -2A, V_{CE} = -2V \\ I_{C} &= -3A, V_{CE} = -2V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-25 -55 -110 -160 -185	-40 -100 -175 -215 -240	mV mV mV mV mV	$I_{C} = -100mA, I_{B} = -10mA$ $I_{C} = -250mA, I_{B} = -10mA$ $I_{C} = -500mA, I_{B} = -10mA$ $I_{C} = -1A, I_{B} = -50mA$ $I_{C} = -1.25A, I_{B} = -100mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	-0.99	-1.10	V	I _C = -1.25A, I _B = -100mA
Base-Emitter Turn-On Voltage	V _{BE(on)}	_	-0.85	-1.0	V	I _C = -1.25A, V _{CE} = -2V
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	_	15	_	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain Bandwidth Product	f⊤	—	220	_	MHz	$I_{C} = -50 \text{mA}, V_{CE} = -10 \text{V}$ f = 100MHz
SWITCHING CHARACTERISTICS						
Turn-On Time	t _{on}	_	50	_	ns	$I_{C} = -1A, V_{CC} = -10V$
Turn-Off Time	t _{off}	_	135		ns	$I_{B1} = -I_{B2} = -100 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.





PNP - Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

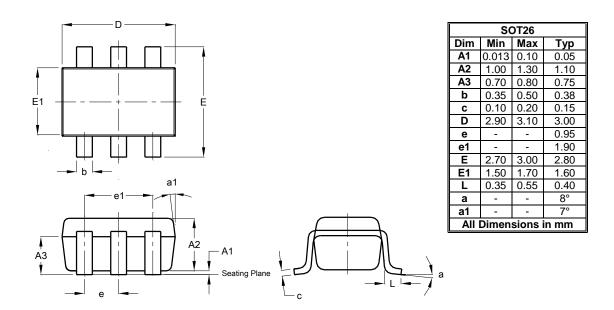






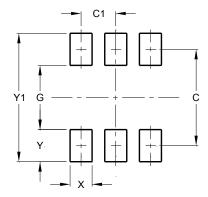
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20





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